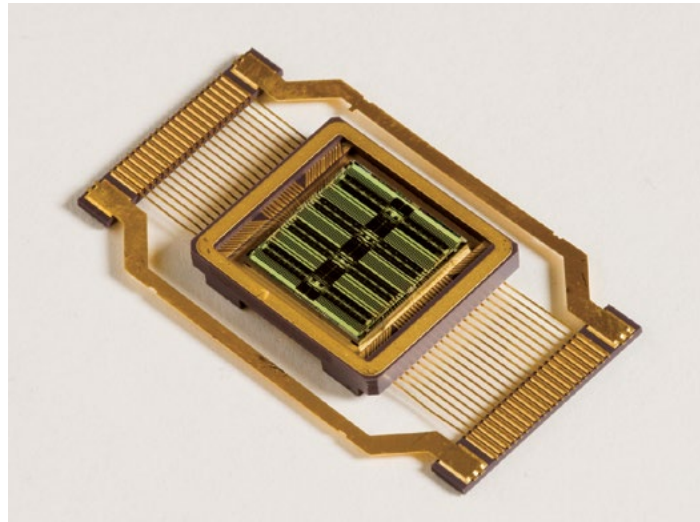


C-RAM™ 2M radiation-hardened non-volatile RAM

Non-volatile memory product

The 256K × 8 radiation-hardened non-volatile RAM with a single-bit error correction (SEC) is a high-performance, 266, 144-word × 8-bit random-access, non-volatile memory with industry-standard functionality.

It is fabricated with BAE Systems' radiation-hardened, 0.25 μm bulk CMOS technology, and is designed for use in systems operating in radiation environments. This NVRAM operates over an extended temperature range and requires a single 3.3V ±10 percent power supply.



System definitions

A0-18 Address input pins that select a particular 8-bit word within the memory array.

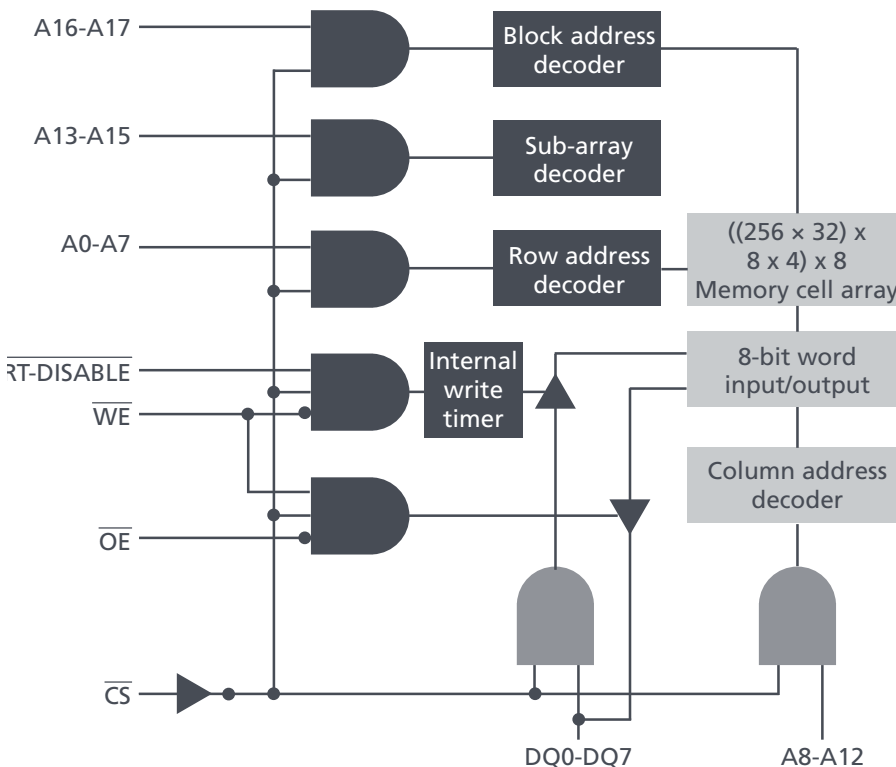
DQ0-7 Bi-directional data pins that serve as data outputs during a read operation and as data inputs during a write operation.

$\overline{\text{CS}}$ Negative-active chip select when low level allows normal read or write operation. When high, $\overline{\text{CS}}$ forces the NVRAM to a precharge condition, holds the data output drivers in a high-impedance state, and disables write operations. If this signal is not used, it must be connected to GND.

$\overline{\text{WE}}$ Negative-active write-enable. When low (and WRT-DISABLE inactive), $\overline{\text{WE}}$ activates a write operation and holds the data output drivers in a high-impedance state. When high, $\overline{\text{WE}}$ allows normal-read operation.

$\overline{\text{OE}}$ Negative-active output-enable. When high, $\overline{\text{OE}}$ holds the data output drivers in a high-impedance state. When low, the data output driver state is defined by $\overline{\text{CS}}$ and $\overline{\text{WE}}$. If this signal is not used, it must be connected to GND.

$\overline{\text{WRT-DISABLE}}$ Negative-active write-disable. When low (power-on reset, PROM mode, etc.), disables write operations while maintaining read-operation availability. When high, $\overline{\text{WRT-DISABLE}}$ permits write operations. If this signal is not used, it must be connected to VDD.



C-RAM family of products

2 Mb single chip

256K x 8 C-RAM

40-lead flatpack
(0.640 x 1.006 inches)

Also available

4 Mb (512K x 8) monolithic
and 20 Mb (512K x 40)
MCM configurations

Key features

Minimum read cycle times

≤ 70 ns

Minimum write-cycle times

< 1000 ns

Single power supply

3.3 V ± 10 percent

Operating temperature range

-40 to 110 degrees Celsius

Low operating power

200 mW (typical) active read
(70 ms)

130 mW (typical) active write
(1000 ns)

60 mW (typical) standby
(maximum)

Write cycle endurance

> 105 cycles

Data retention

0.3 years at 90 degrees
Celsius

1.1 years at 85 degrees
Celsius

3.8 years at 80 degrees
Celsius

13.5 years at 75 degrees
Celsius

50 years at 70 degrees
Celsius

Radiation levels

Total ionizing dose:
> 5 × 10⁵ rad (Si)

Single event upset:
1 × 10⁻¹¹ upsets/bit day

Neutron fluence:
> 1 × 10¹³ particles/cm²

Latchup-immune:
≤ 120 MeV-cm²/mg

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